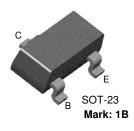


SEMICONDUCTOR®

# **MMBT2222**

## **NPN General Purpose Amplifier**

Sourced from process 19.



## Absolute Maximum Ratings\* $T_a=25^{\circ}C$ unless otherwise noted

Symbol	Parameter	Ratings	Units	
/ <sub>CEO</sub>	Collector-Emitter Voltage	30	V	
/ <sub>CBO</sub>	Collector-Base Voltage	60	V	
/ <sub>EBO</sub>	Emitter-Base Voltage	5.0	V	
С	Collector Current - Continuous	0.6	А	
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Junction Temperature Range	-55 ~ 150	°C	

\* This ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

### NOTES:

1) These rating are based on a maximum junction temperature of 150 degrees C.
2) These are steady limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

## **Electrical Characteristics** $T_a=25^{\circ}C$ unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Max.	Units
Off Charac	cteristics				
V <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage *	$I_{\rm C} = 10 {\rm mA}, I_{\rm B} = 0$	30		V
V <sub>(BR)CBO</sub>	Collector-Base Breakdown Voltage	$I_{\rm C} = 10\mu {\rm A}, I_{\rm E} = 0$	60		V
V <sub>(BR)EBO</sub>	Emitter-Base Breakdown Voltage	$I_{\rm E} = 10 \mu {\rm A}, I_{\rm C} = 0$	5.0		V
I <sub>CBO</sub>	Collector Cutoff Current	$V_{CB} = 50V, I_{E} = 0$		10	μA
		$V_{CB} = 50V, I_E = 0, T_a = 125^{\circ}C$		10	μΑ
I <sub>EBO</sub>	Emitter Cutoff Current	$V_{EB} = 3.0V, I_{C} = 0$		10	nA
On Charac	teristics				
h <sub>FE</sub>	DC Current Gain	I <sub>C</sub> = 0.1mA, V <sub>CE</sub> = 10V	35		
		$I_{C} = 1.0 \text{mA}, V_{CE} = 10 \text{V}$	50		
		I <sub>C</sub> = 10mA, V <sub>CE</sub> = 10V	75		
		I <sub>C</sub> = 150mA, V <sub>CE</sub> = 10V *	100	300	
		$I_{C} = 150 \text{mA}, V_{CE} = 1.0 \text{V}^{*}$	50		
		$I_{C} = 500 \text{mA}, V_{CE} = 10 \text{V}^{*}$	30		
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage *	I <sub>C</sub> = 150mA, I <sub>B</sub> = 15V		0.4	V
- ()		$I_{\rm C} = 500 {\rm mA}, I_{\rm B} = 50 {\rm V}$		1.6	
V <sub>BE(sat)</sub>	Base-Emitter Saturation Voltage	I <sub>C</sub> = 150mA, I <sub>B</sub> = 15V		1.3	V
. /		I <sub>C</sub> = 500mA, I <sub>B</sub> = 50V		2.6	

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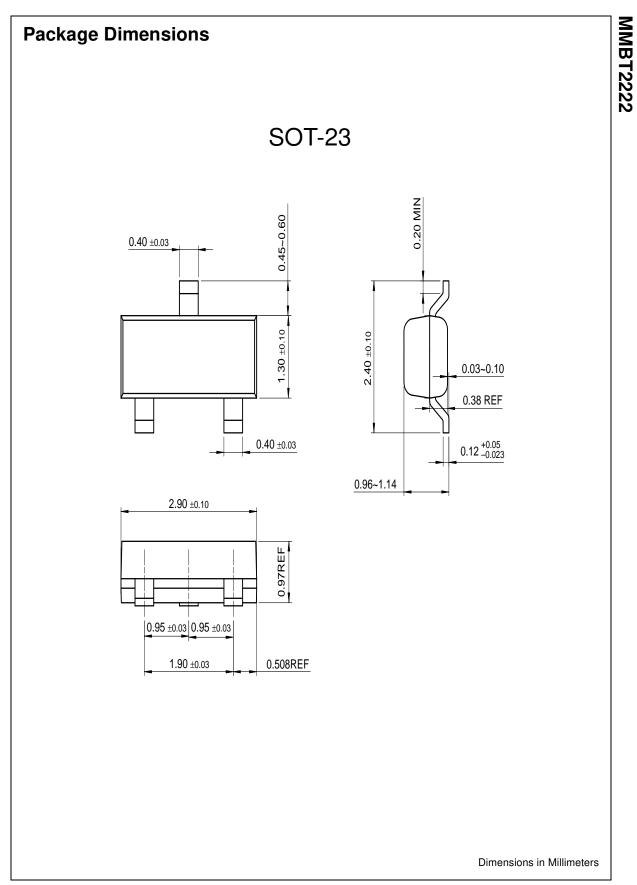
Electrical Characteristics (Continued) T <sub>a</sub> =25°C unless otherwise noted						
Symbol	Parameter	Test Condition	Min.	Max.	Units	
Small Signal Characteristics						
f <sub>T</sub>	Curent Gain Bandwidth Product	I <sub>C</sub> = 20mA, V <sub>CE</sub> = 20V, f = 100MHz	250			
C <sub>obo</sub>	Output Capacitance	V <sub>CB</sub> = 10V, I <sub>E</sub> = 0, f = 1MHz		8.0	pF	
C <sub>ibo</sub>	Input Capacitance	V <sub>EB</sub> = 0.5V, I <sub>C</sub> = 0, f = 1MHz		30	pF	
Switching	Characteristics					
t <sub>d</sub>	Delay Time	$V_{CC} = 30V, V_{BE(OFF)} = 0.5V,$		10	ns	
t <sub>r</sub>	Rise Time	I <sub>C</sub> = 150mA, I <sub>B1</sub> = 15mA		25	ns	
ts	Storage Time	V <sub>CC</sub> = 30V, I <sub>C</sub> = 150mA,		225	ns	
t <sub>f</sub>	Fall Time	$I_{B1} = I_{B2} = 15mA$		60	ns	

\* Pulse Test: Pulse Width  $\leq$  300µs, Duty Cycle  $\leq$  2.0%

# Thermal Characteristics $T_a=25^{\circ}C$ unless otherwise noted

Symbol	Parameter	Max.	Units
PD	Total Device Dissipation	350	mW
-	Derate above 25°C	2.8	mW/°C
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	357	°C/W

\* Device mounted on FR-4PCB 1.6"  $\times$  1.6"  $\times$  0.06".



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